

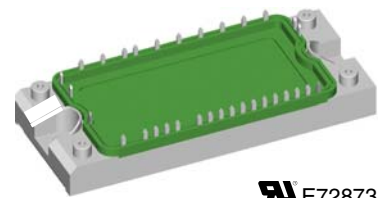
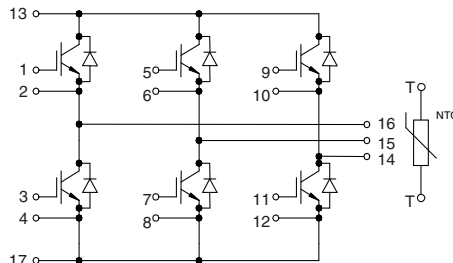
# IGBT Modules

## Sixpack

Short Circuit SOA Capability  
 Square RBSOA

$I_{C25} = 72 \text{ A}$   
 $V_{CES} = 600 \text{ V}$   
 $V_{CE(sat) \text{ typ.}} = 1.9 \text{ V}$

<b>Type:</b>	NTC - Option:
<b>MWI 50-06 A7</b>	without NTC
<b>MWI 50-06 A7T</b>	with NTC



See outline drawing for pin arrangement

### IGBTs

Symbol	Conditions	Maximum Ratings	
$V_{CES}$	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	600	V
$V_{GES}$		$\pm 20$	V
$I_{C25}$	$T_C = 25^{\circ}\text{C}$	72	A
$I_{C80}$	$T_C = 80^{\circ}\text{C}$	50	A
<b>RBSOA</b>	$V_{GE} = \pm 15 \text{ V}; R_G = 22 \Omega; T_{VJ} = 125^{\circ}\text{C}$ Clamped inductive load; $L = 100 \mu\text{H}$	$I_{CM} = 100$ $V_{CEK} \leq V_{CES}$	A
$t_{SC}$ <b>(SCSOA)</b>	$V_{CE} = V_{CES}; V_{GE} = \pm 15 \text{ V}; R_G = 22 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	$\mu\text{s}$
$P_{tot}$	$T_C = 25^{\circ}\text{C}$	225	W

### Features

- NPT IGBT technology
- low saturation voltage
- low switching losses
- switching frequency up to 30 kHz
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- ultra fast free wheeling diodes
- solderable pins for PCB mounting
- package with copper base plate

### Advantages

- space savings
- reduced protection circuits
- package designed for wave soldering

### Typical Applications

- AC motor control
- AC servo and robot drives
- power supplies

Symbol	Conditions	Characteristic Values ( $T_{VJ} = 25^{\circ}\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$V_{CE(sat)}$	$I_C = 50 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.9	2.4	V	
$V_{GE(th)}$	$I_C = 1 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V	
$I_{CES}$	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.7		0.6 mA	
$I_{GES}$	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			200 nA	
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 300 \text{ V}; I_C = 50 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 22 \Omega$		50	ns	
$E_{on}$			60	ns	
$E_{off}$			300	ns	
				30	ns
				2.3	mJ
$C_{ies}$	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		2800	pF	
$Q_{Gon}$	$V_{CE} = 300 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 50 \text{ A}$		120	nC	
$R_{thJC}$	(per IGBT)			0.55 K/W	

**Diodes**

Symbol	Conditions	Maximum Ratings	
$I_{F25}$	$T_C = 25^\circ\text{C}$	72	A
$I_{F80}$	$T_C = 80^\circ\text{C}$	45	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$V_F$	$I_F = 50\text{ A}; V_{GE} = 0\text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	1.6	1.8	V
$I_{RM}$	$I_F = 30\text{ A}; di_F/dt = -500\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 300\text{ V}; V_{GE} = 0\text{ V}$	25		A
$t_{rr}$		90		ns
$R_{thJC}$	(per diode)			1.19 K/W

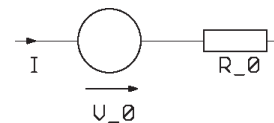
**Temperature Sensor NTC (MWI ... A7T version only)**

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{25}$	$T = 25^\circ\text{C}$	4.75	5.0	5.25 k $\Omega$
$B_{25/50}$			3375	K

**Module**

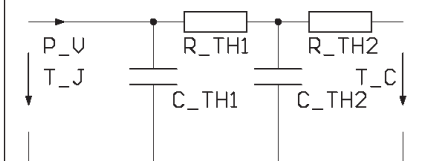
Symbol	Conditions	Maximum Ratings	
$T_{VJ}$		-40...+150	$^\circ\text{C}$
$T_{stg}$		-40...+125	$^\circ\text{C}$
$V_{ISOL}$	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	2500	V~
$M_d$	Mounting torque (M5)	2.7 - 3.3	Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{pin-chip}$			5	m $\Omega$
$d_S$	Creepage distance on surface	6		mm
$d_A$	Strike distance in air	6		mm
$R_{thCH}$	with heatsink compound		0.02	K/W
<b>Weight</b>			180	g

**Equivalent Circuits for Simulation**
**Conduction**


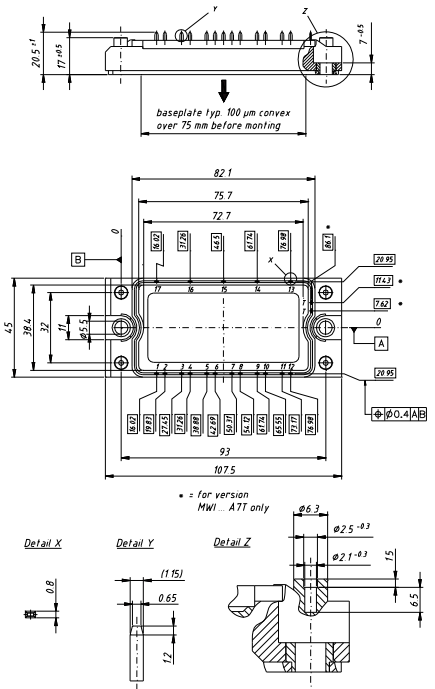
IGBT (typ. at  $V_{GE} = 15\text{ V}; T_J = 125^\circ\text{C}$ )  
 $V_0 = 0.82\text{ V}; R_0 = 28\text{ m}\Omega$

Free Wheeling Diode (typ. at  $T_J = 125^\circ\text{C}$ )  
 $V_0 = 0.89\text{ V}; R_0 = 8\text{ m}\Omega$

**Thermal Response**


IGBT (typ.)  
 $C_{th1} = 0.201\text{ J/K}; R_{th1} = 0.42\text{ K/W}$   
 $C_{th2} = 1.252\text{ J/K}; R_{th2} = 0.131\text{ K/W}$

Free Wheeling Diode (typ.)  
 $C_{th1} = 0.116\text{ J/K}; R_{th1} = 0.973\text{ K/W}$   
 $C_{th2} = 0.88\text{ J/K}; R_{th2} = 0.217\text{ K/W}$

**Dimensions in mm (1 mm = 0.0394")**


Higher magnification on page B3 - 72

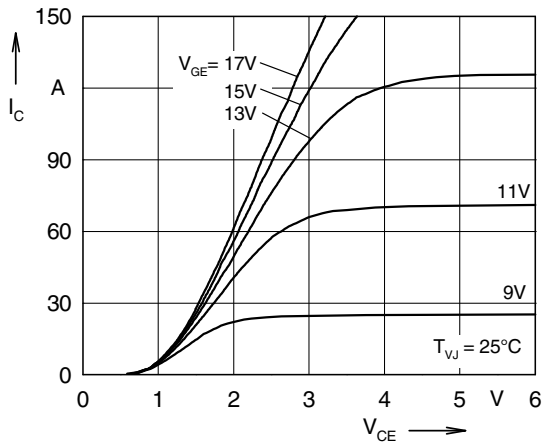


Fig. 1 Typ. output characteristics

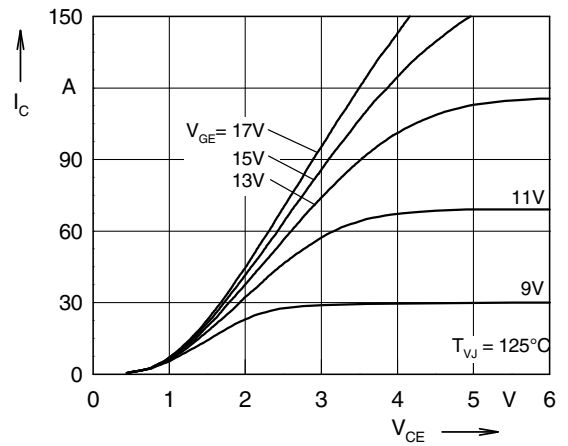


Fig. 2 Typ. output characteristics

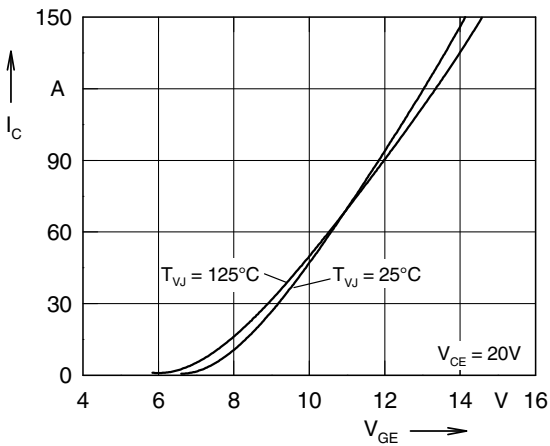


Fig. 3 Typ. transfer characteristics

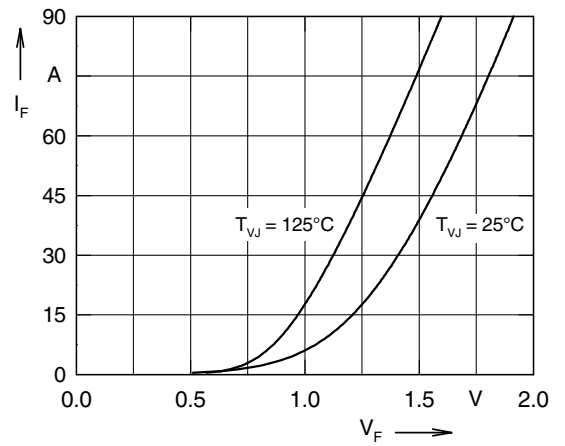


Fig. 4 Typ. forward characteristics of free wheeling diode

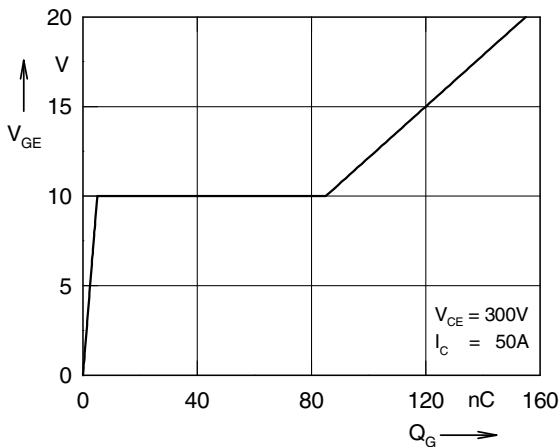


Fig. 5 Typ. turn on gate charge

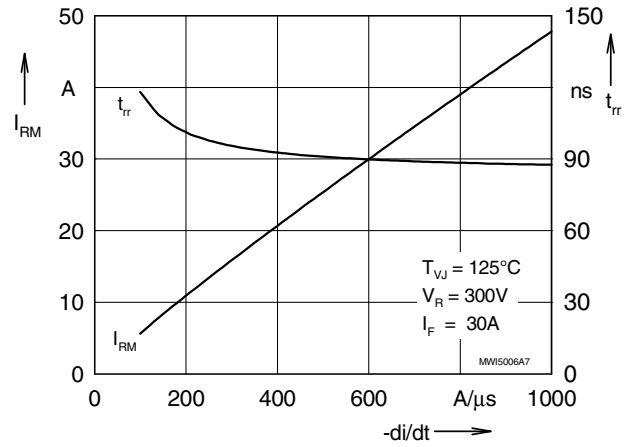


Fig. 6 Typ. turn off characteristics of free wheeling diode

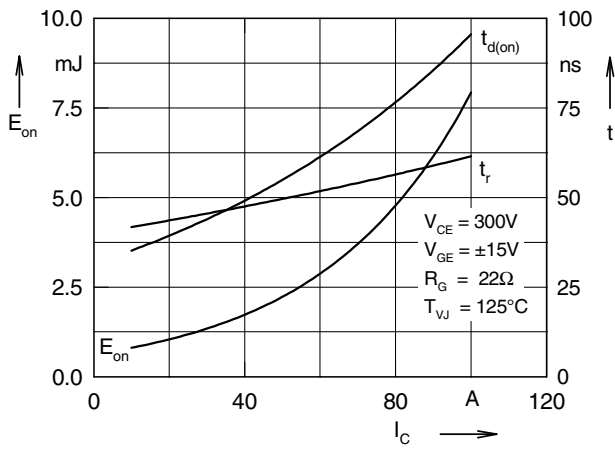


Fig. 7 Typ. turn on energy and switching times versus collector current

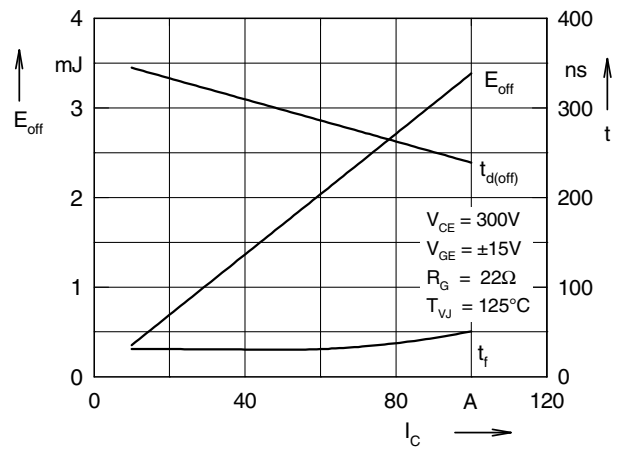


Fig. 8 Typ. turn off energy and switching times versus collector current

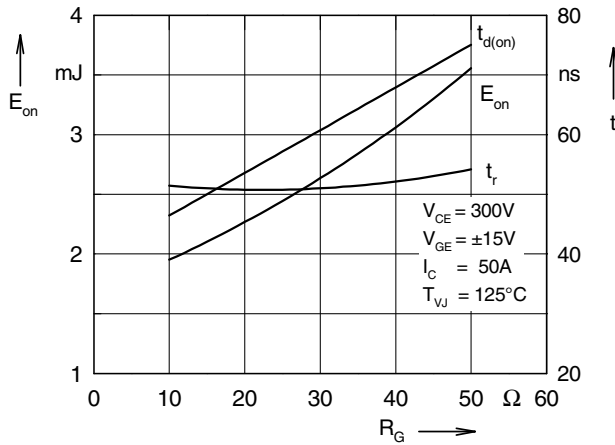


Fig. 9 Typ. turn on energy and switching times versus gate resistor

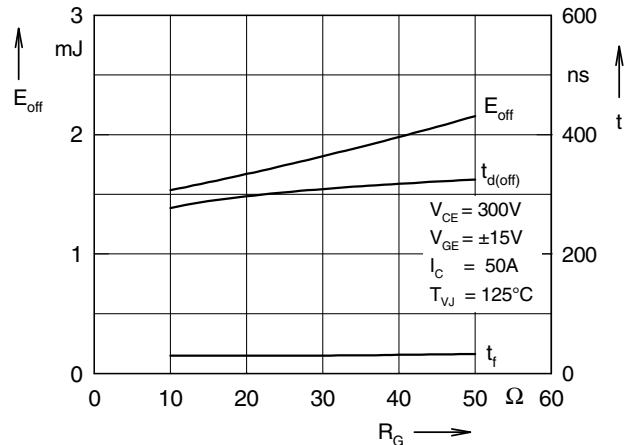


Fig.10 Typ. turn off energy and switching times versus gate resistor

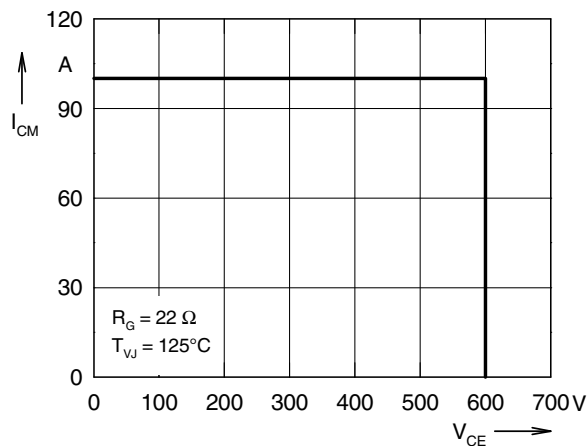


Fig. 11 Reverse biased safe operating area RBSOA

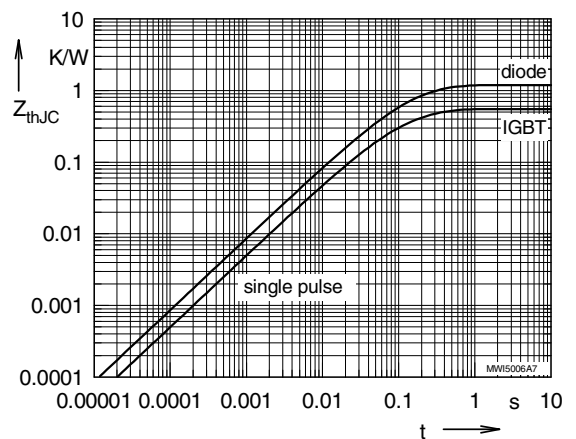


Fig. 12 Typ. transient thermal impedance